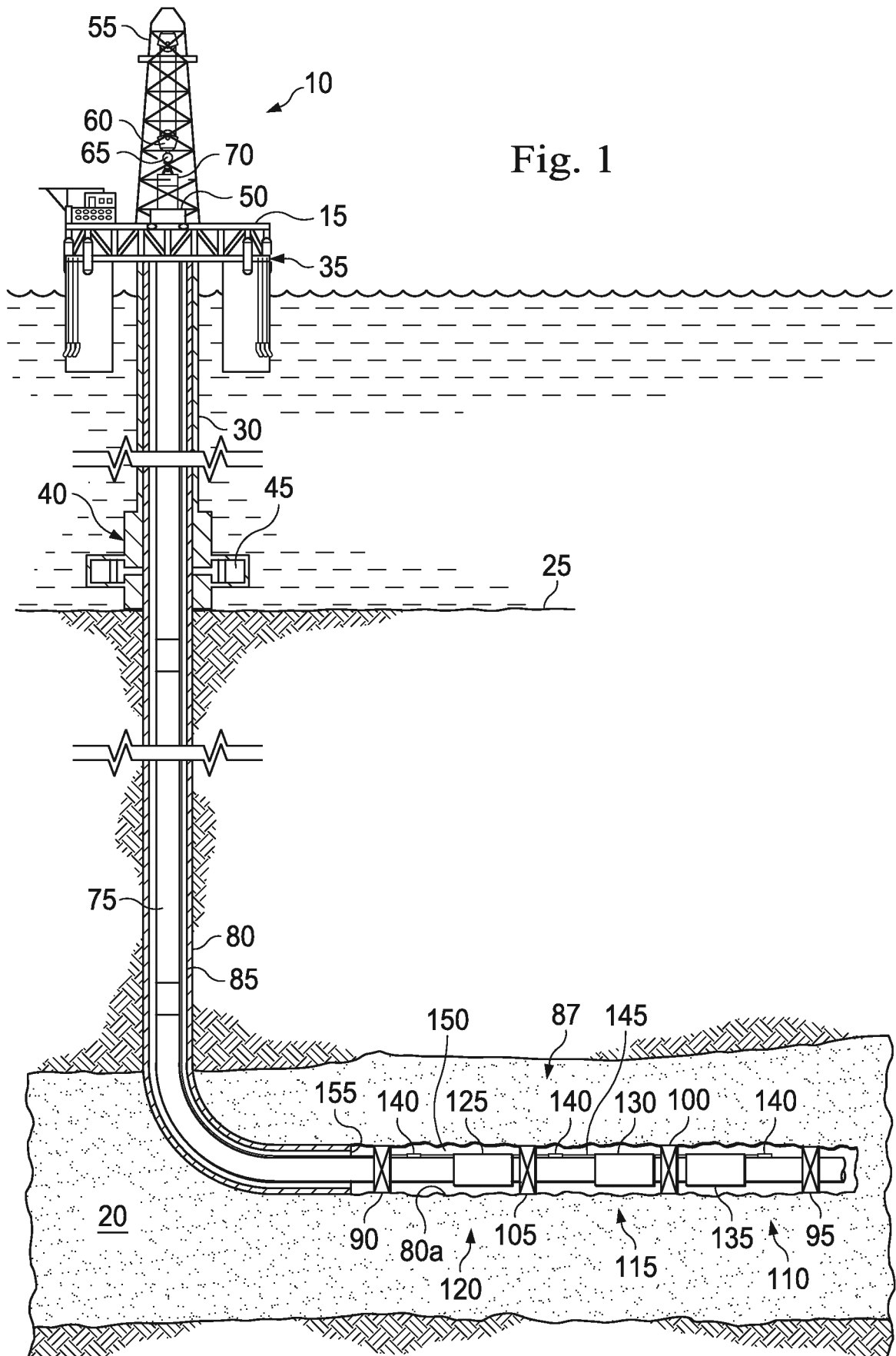


Fig. 1



A detailed cross-sectional diagram of a semiconductor device. The structure consists of several stacked layers. At the bottom is a substrate labeled 75. Above it are alternating horizontal layers of different materials, indicated by diagonal hatching patterns. Labels 145, 166, and 185 point to specific layers. A central vertical stack of components includes a rectangular block 175, a smaller block 180 above it, and another block 173 below 180. Block 173 has two sub-regions labeled 173a and 173b. To the right of this central stack is a large rectangular region labeled 150, which sits on top of layer 185. Further to the right is a thin layer labeled 385, followed by a hatched layer labeled 95. The entire assembly is enclosed within a larger frame or housing, with wavy break lines at the top and bottom edges.

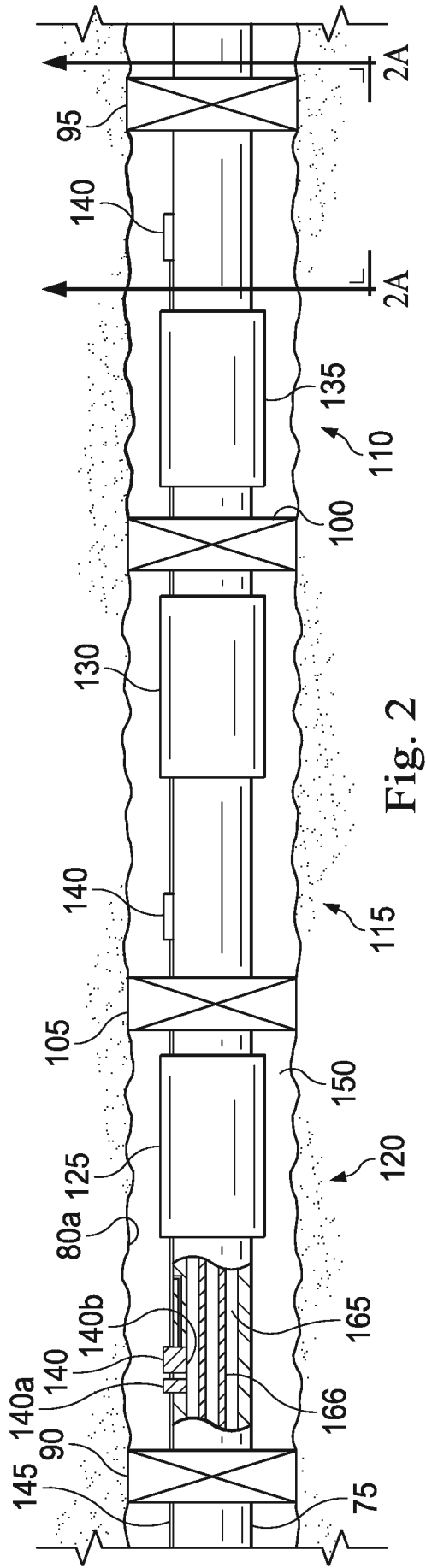


Fig. 2

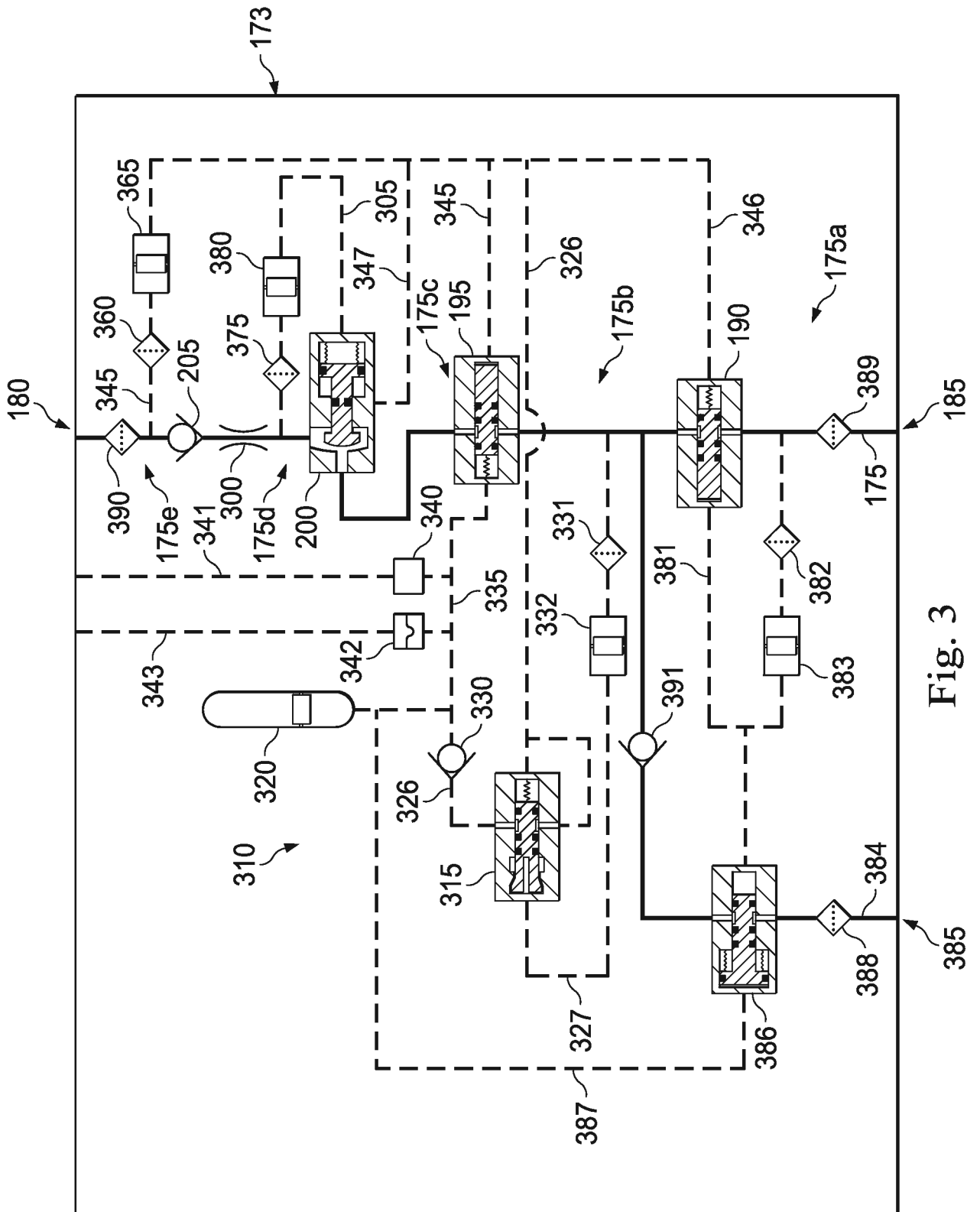


Fig. 3

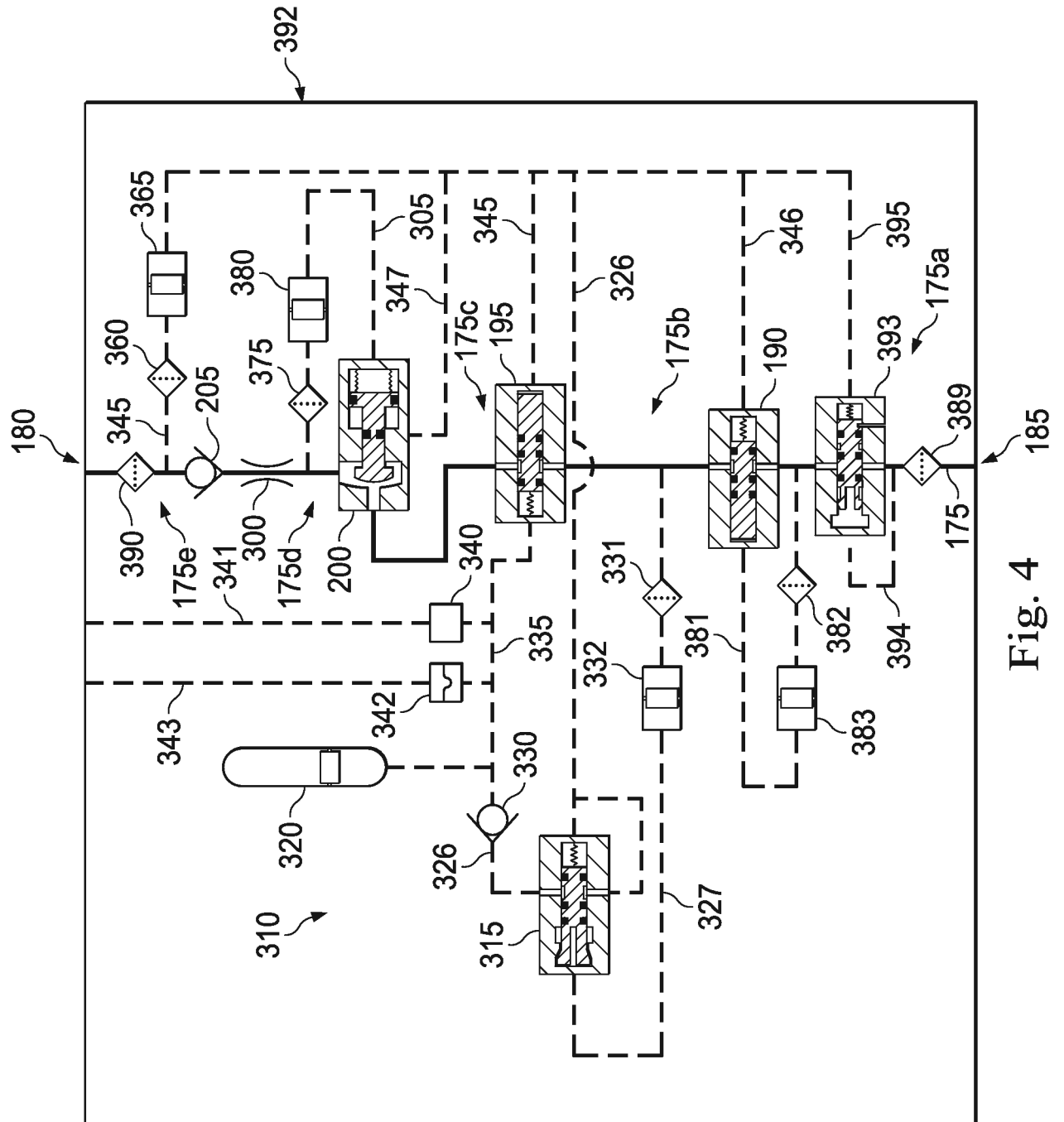


Fig. 4

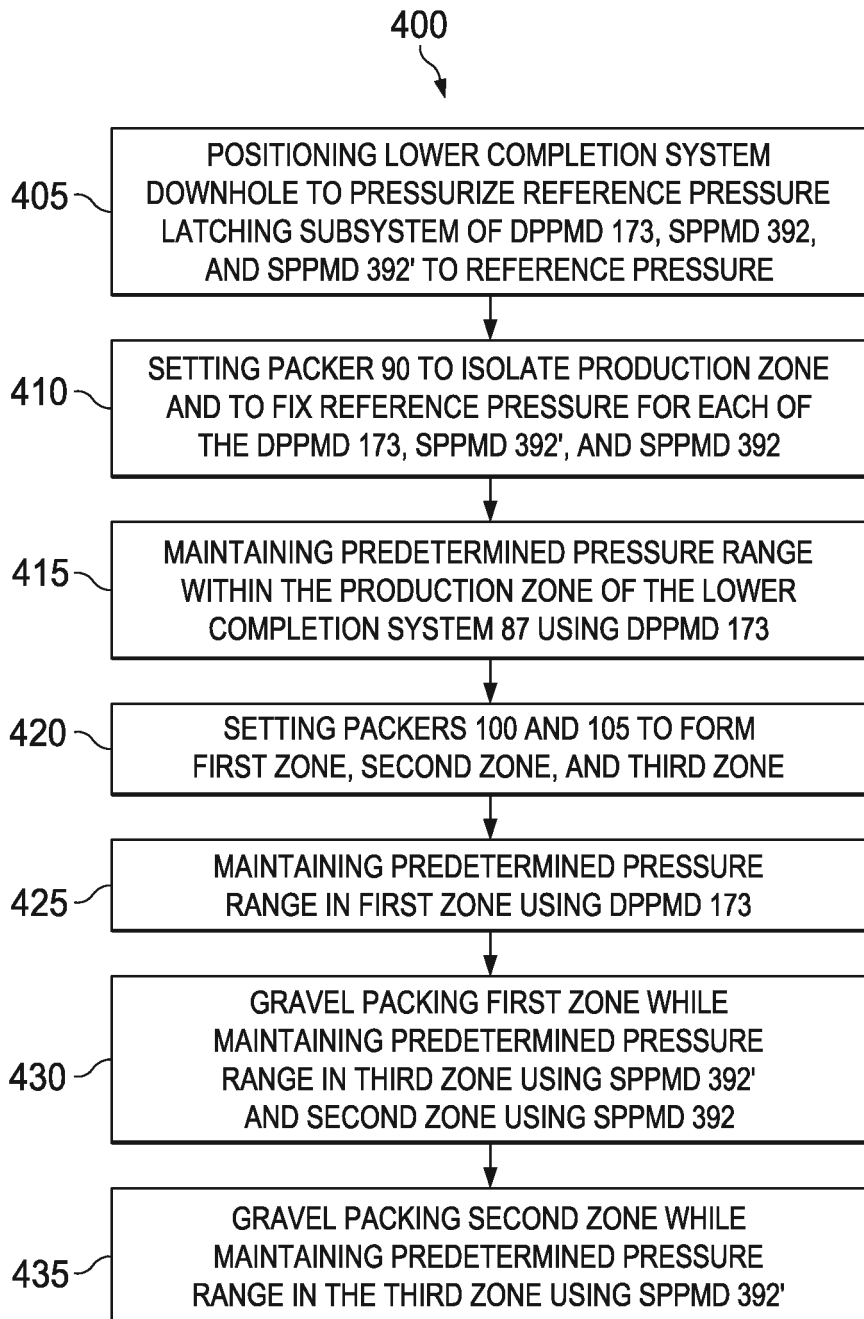
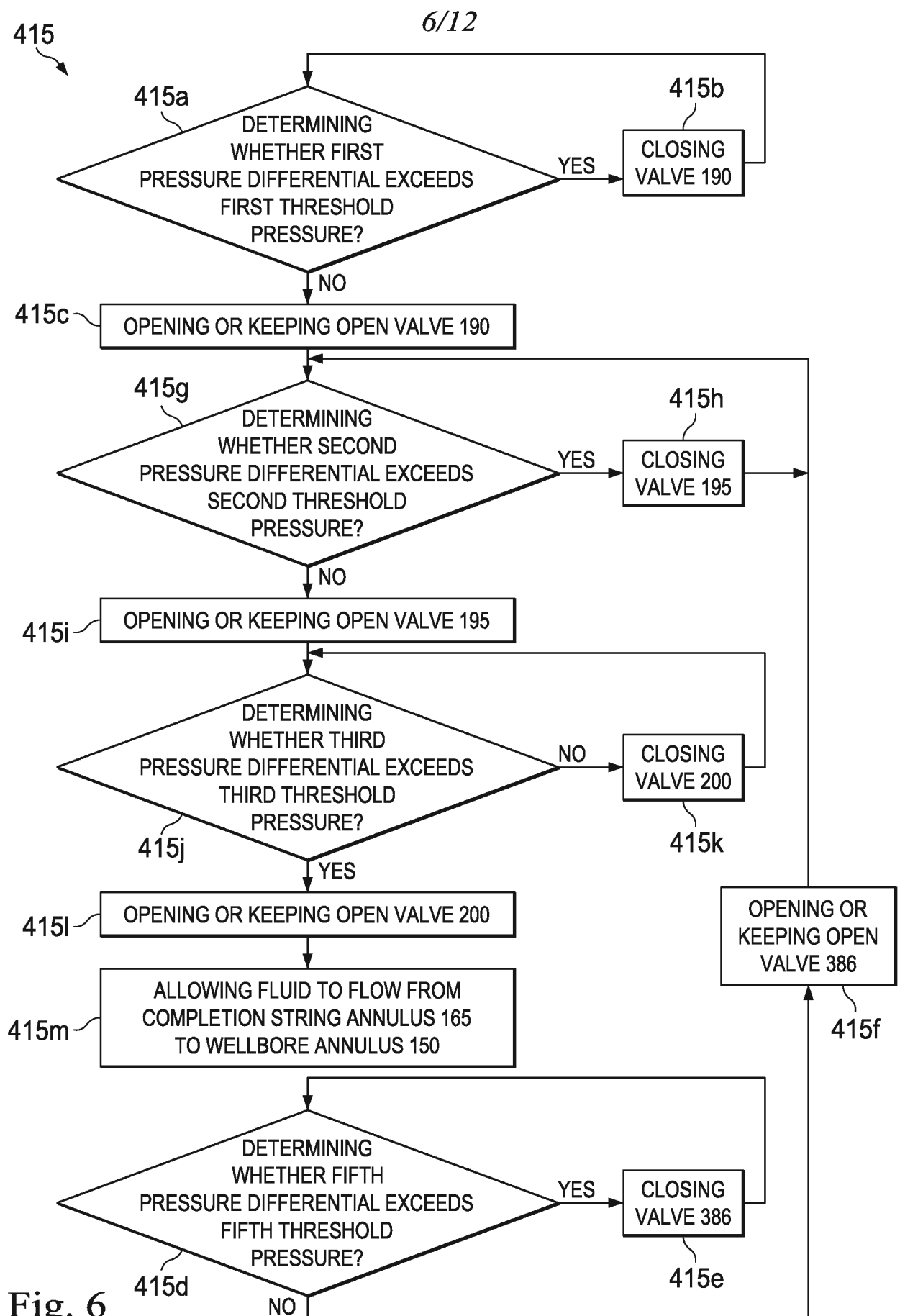


Fig. 5



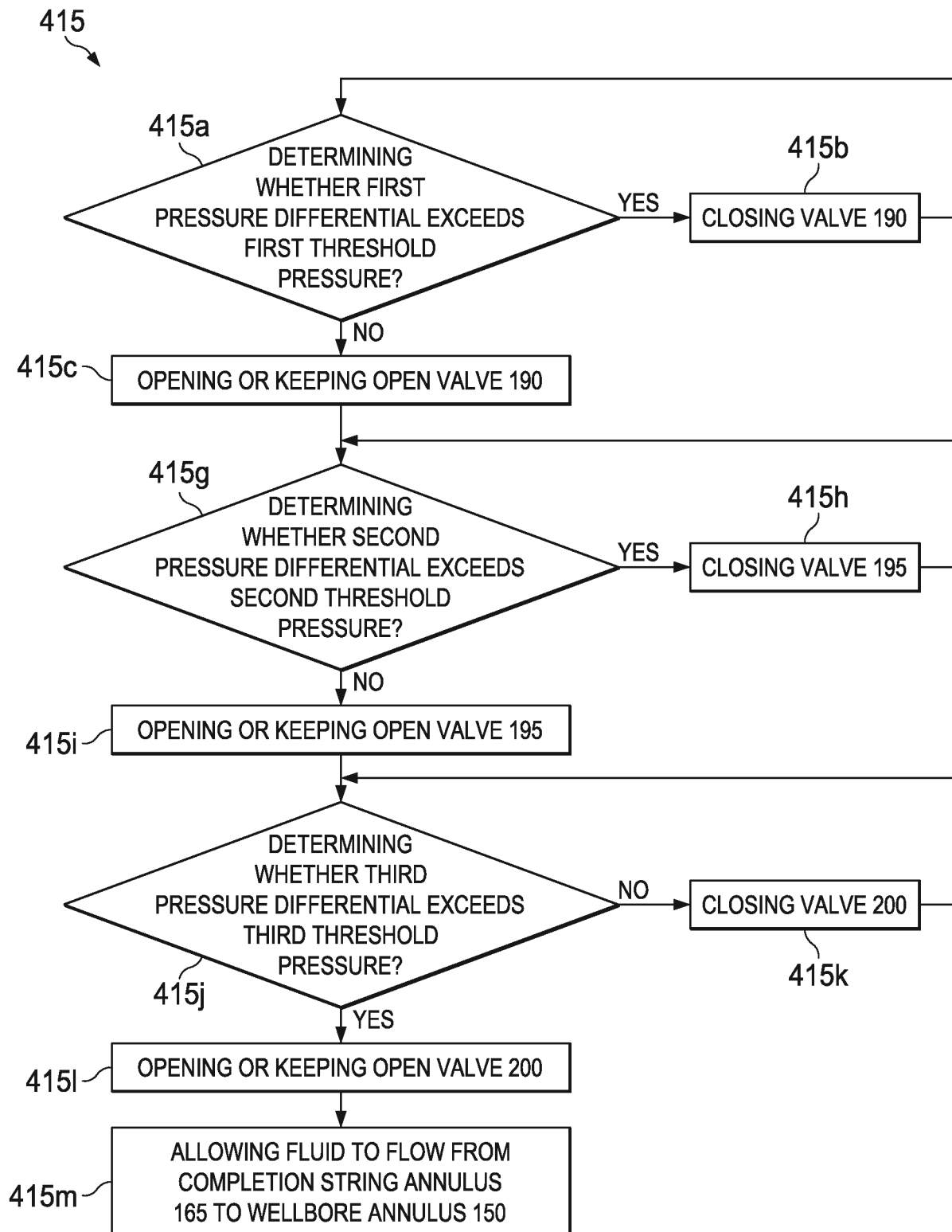
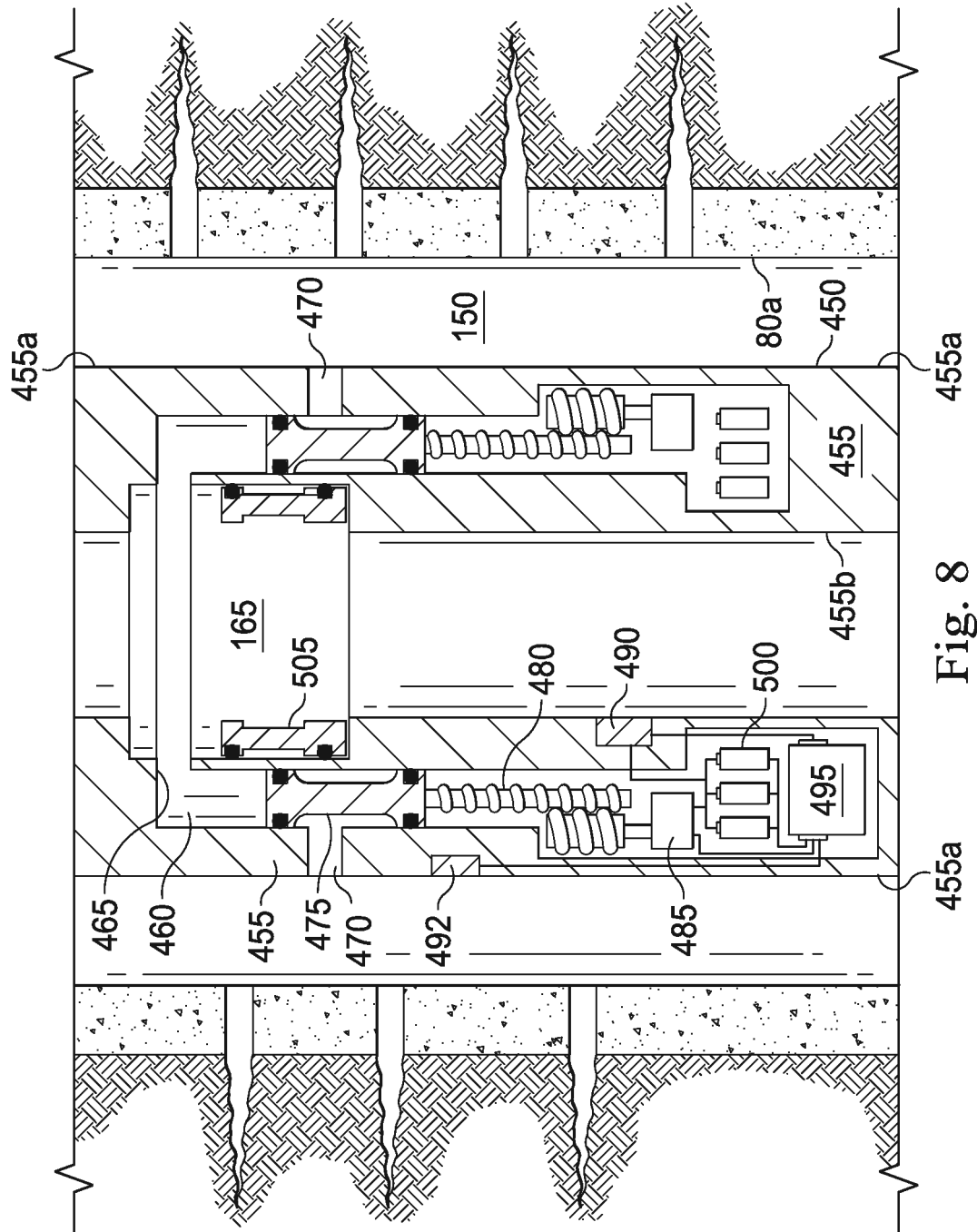


Fig. 7



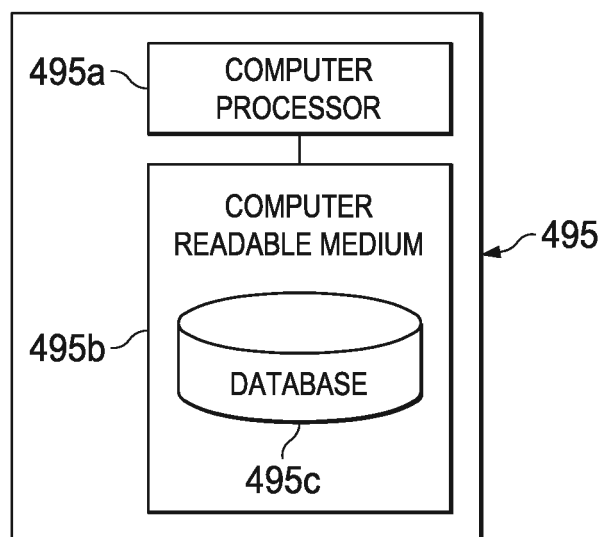


Fig. 8A

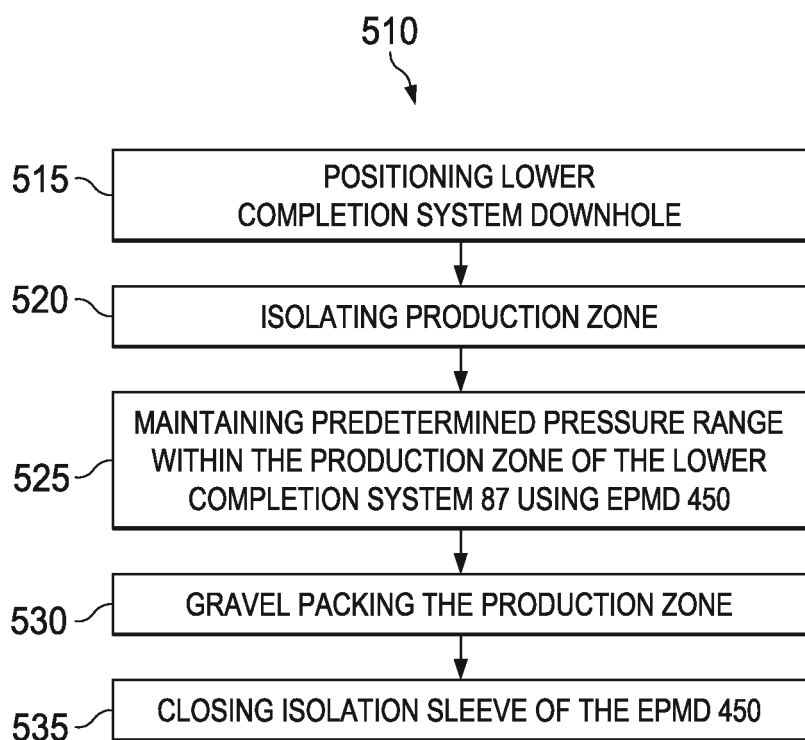
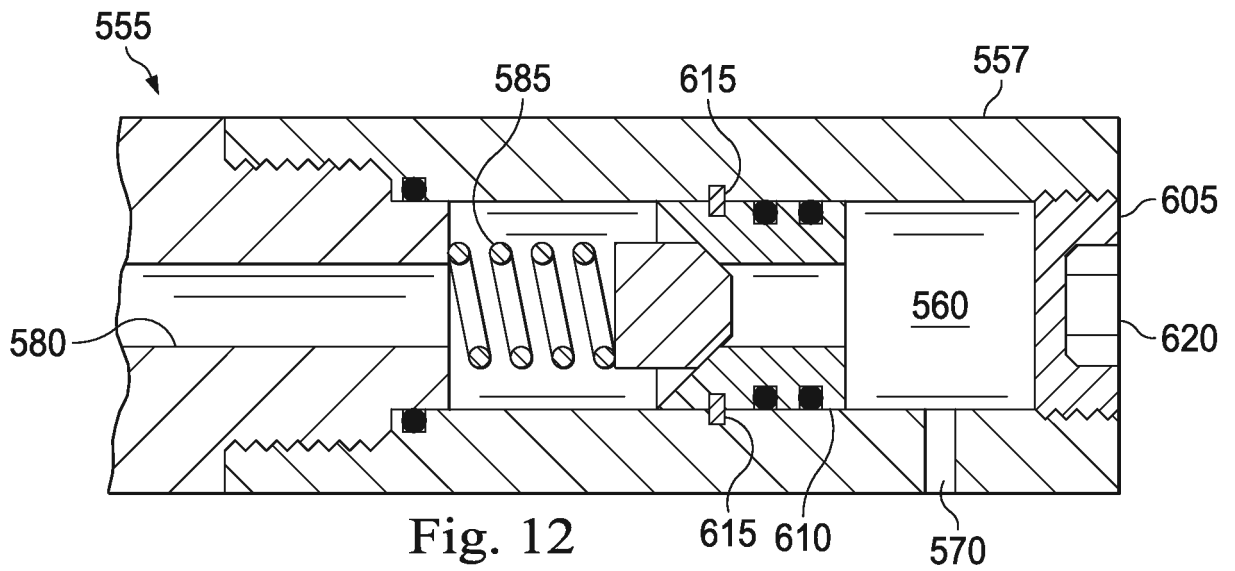
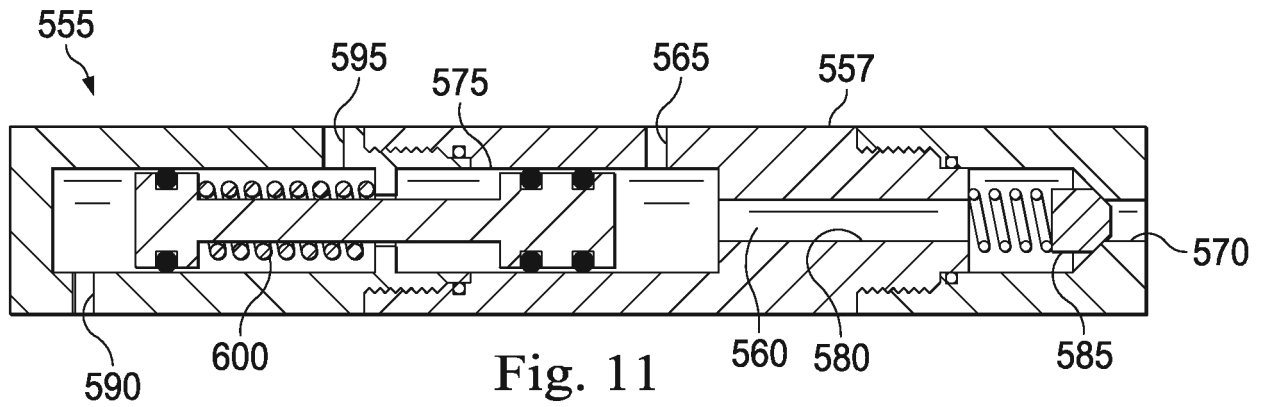
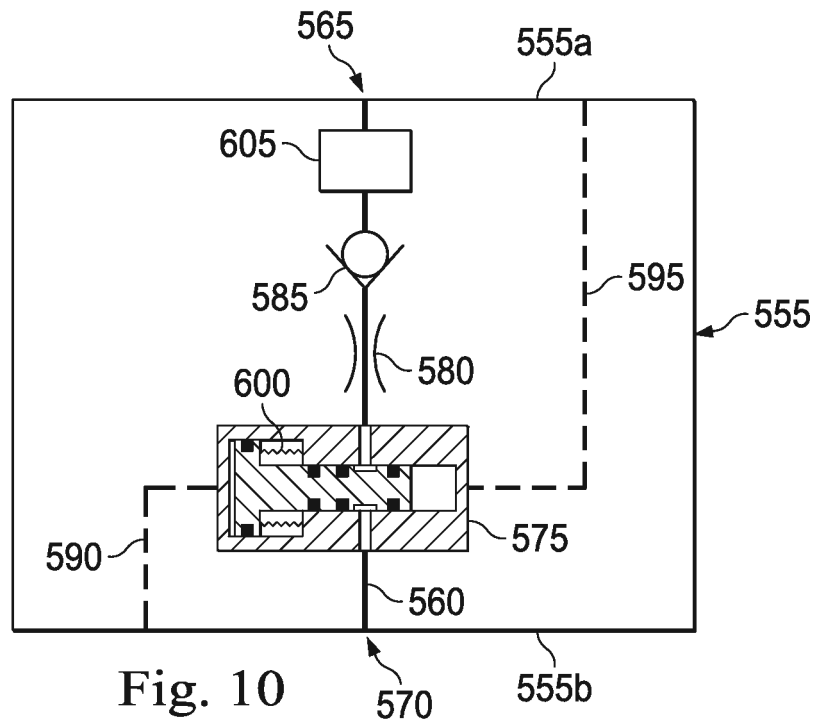
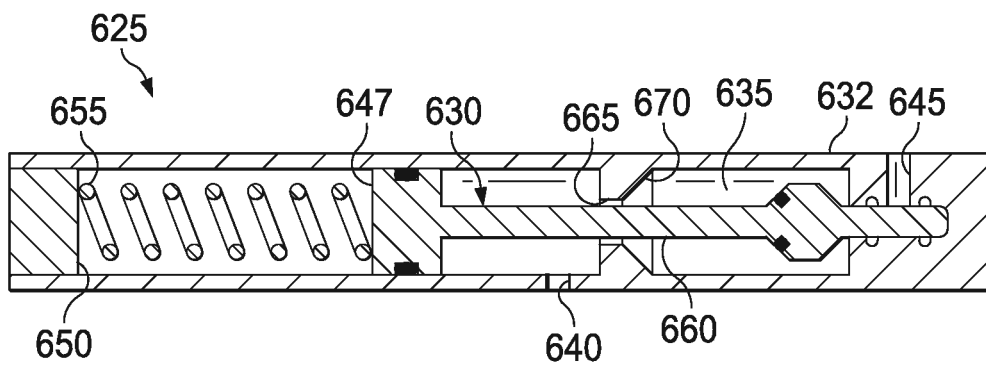
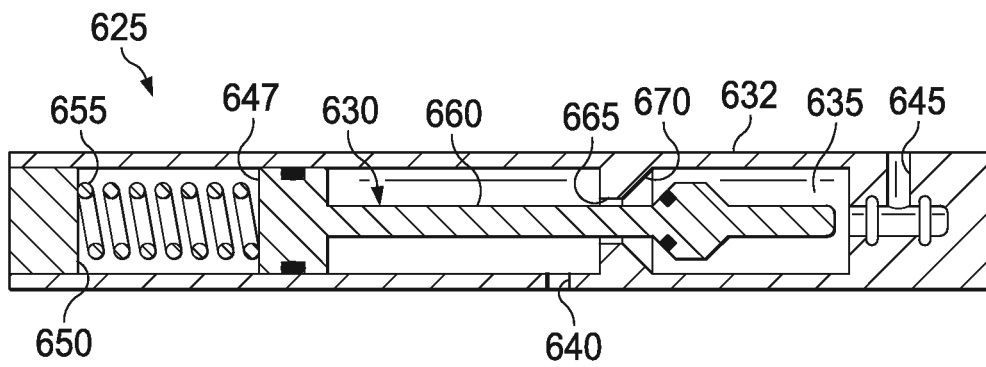
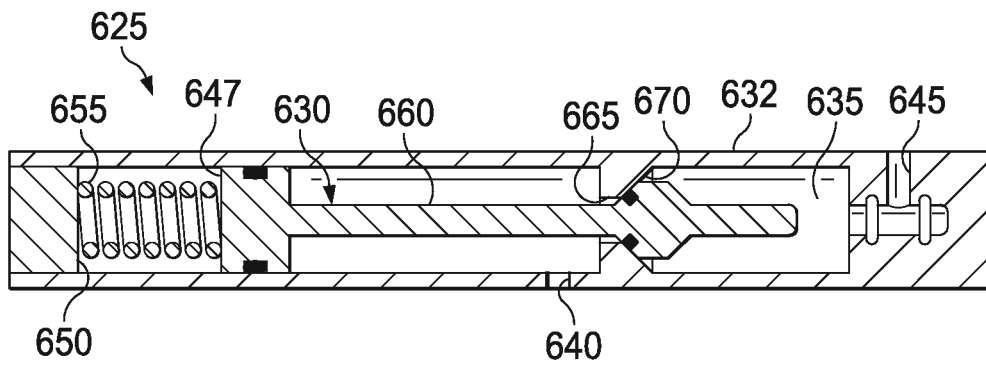
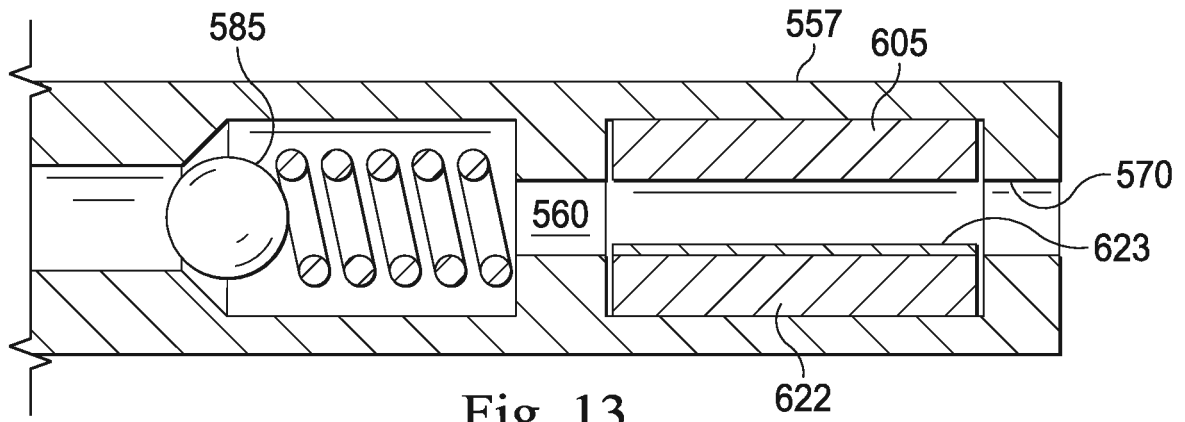


Fig. 9

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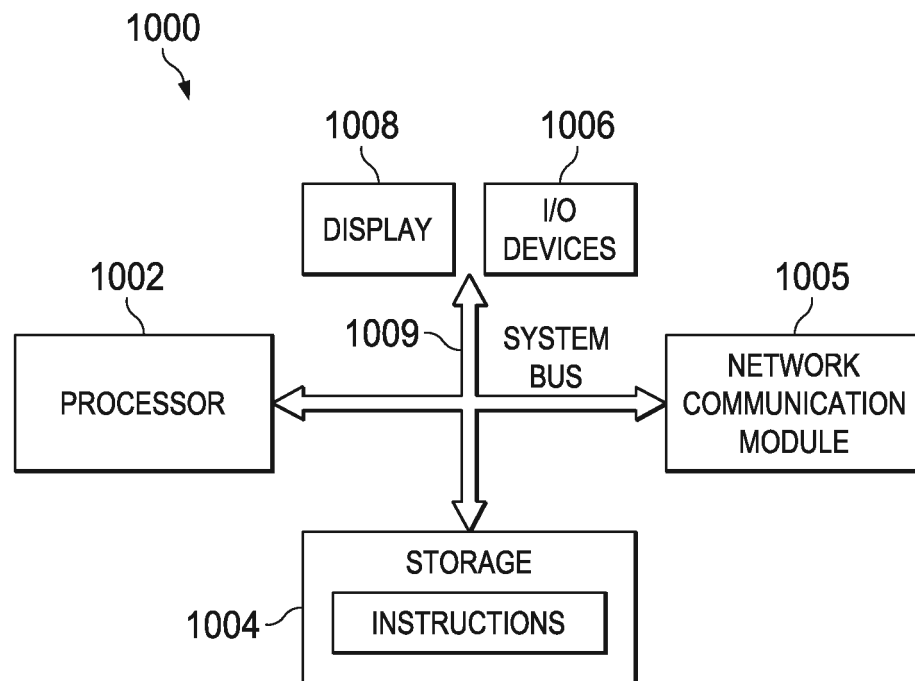


Fig. 17